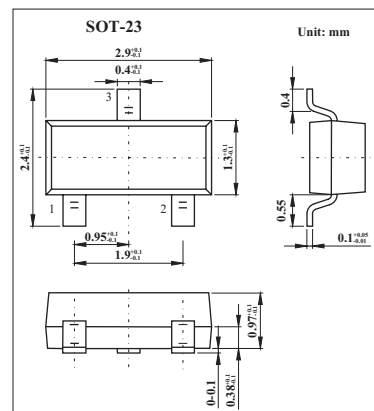


Silicon Schottky Barrier Diode

HRW0202B

■ Features

- Low forward voltage drop and suitable for high efficiency rectifying.
- MPAK package is suitable for high density surface mounting and high speed assembly.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	20	V
Average rectified current	I_O	200	mA
Non-repetitive peak forward surge current	I_{FSM}	3	A
Junction temperature	T_J	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to + 125	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	V_F	$I_F = 100\text{ mA}$			0.42	V
Reverse current	I_R	$V_R = 20\text{ V}$			10	$\mu\text{ A}$
Thermal resistance	$T_{sh(j-a)}$	Polyimide board		400		$^\circ\text{C/W}$

■ Marking

Marking	S18
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